

Fig. 3-33 The mobility of different laser frequency with pre treatment clean of HF+O3

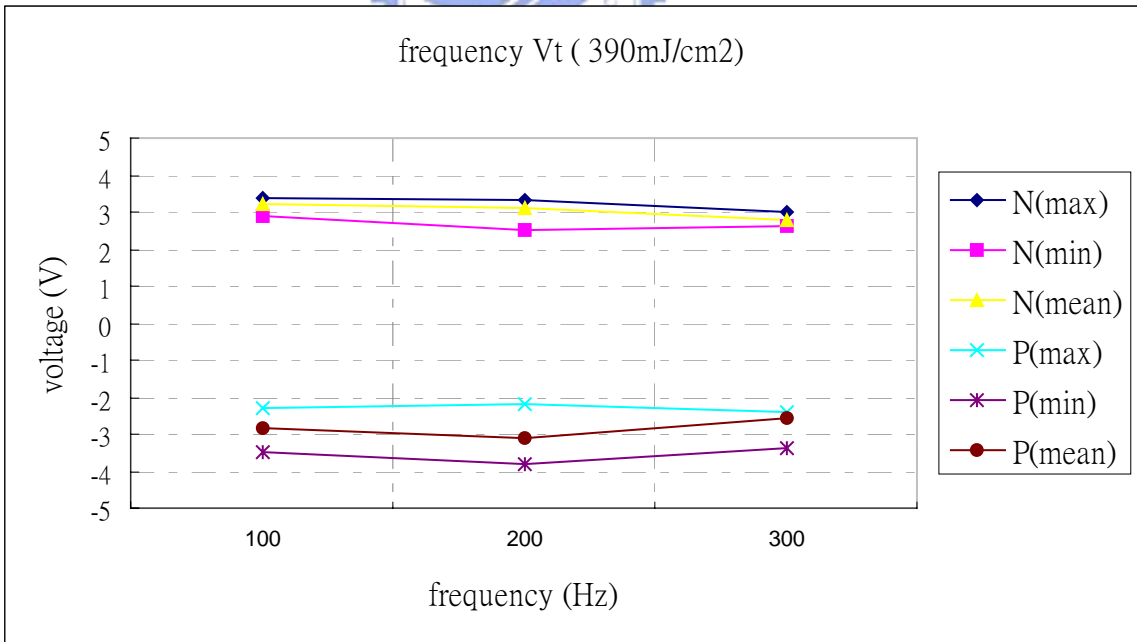


Fig. 3-34 The thresholds voltage of different laser frequency with pre treatment clean of HF+O3

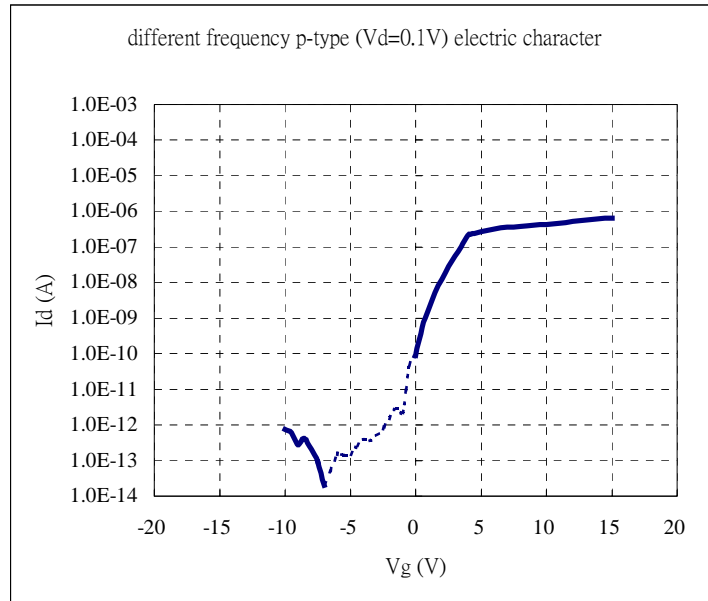


Fig. 3-35 The transfer characteristics of p type ELA poly-Silicon TFTs. Laser frequency 300Hz, laser energy density 390mJ/cm², W/L = 6μm/12μm, Vt -2.8 V, Ufe 97 cm²/V•sec, Ioff 2.93E-13A, SS 0.22 and on/off current ratio 6.1E+6

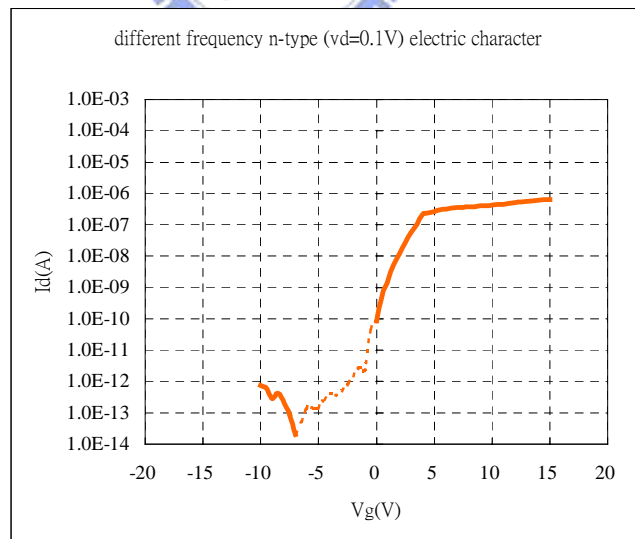


Fig. 3-36 The transfer characteristics of n type ELA poly-Silicon TFTs. Laser frequency 300Hz, laser energy density 390mJ/cm², W/L = 6μm/12μm, Vt 3.0V, Ufe 124 cm²/V•sec, Ioff 1.23E-13A, SS 0.62 and on/off current ratio 5.2E+6

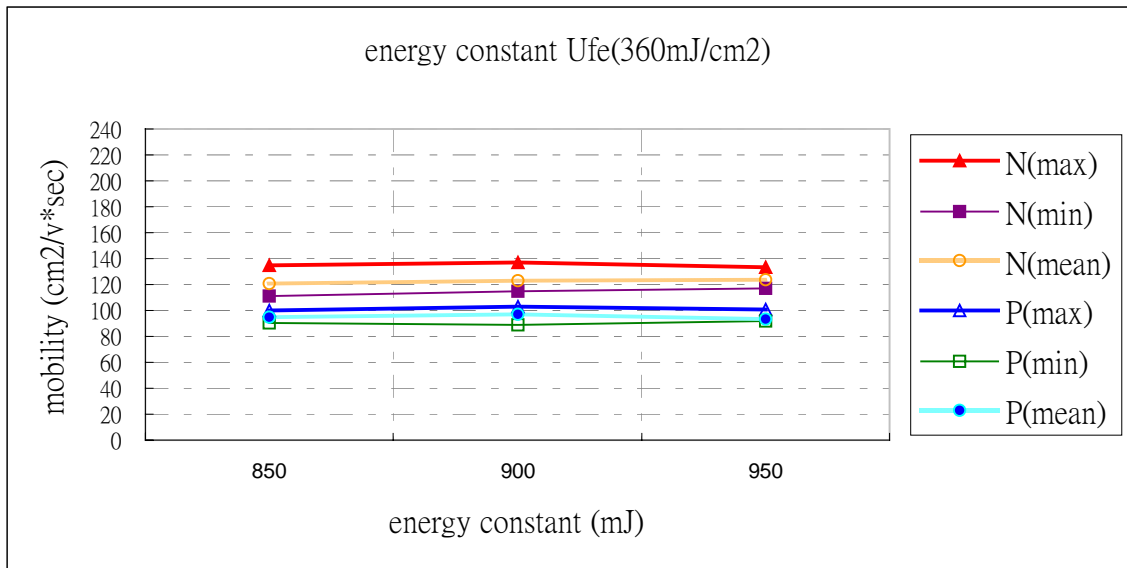


Fig. 3-37 The mobility of different laser energy with pre treatment clean of HF+O3

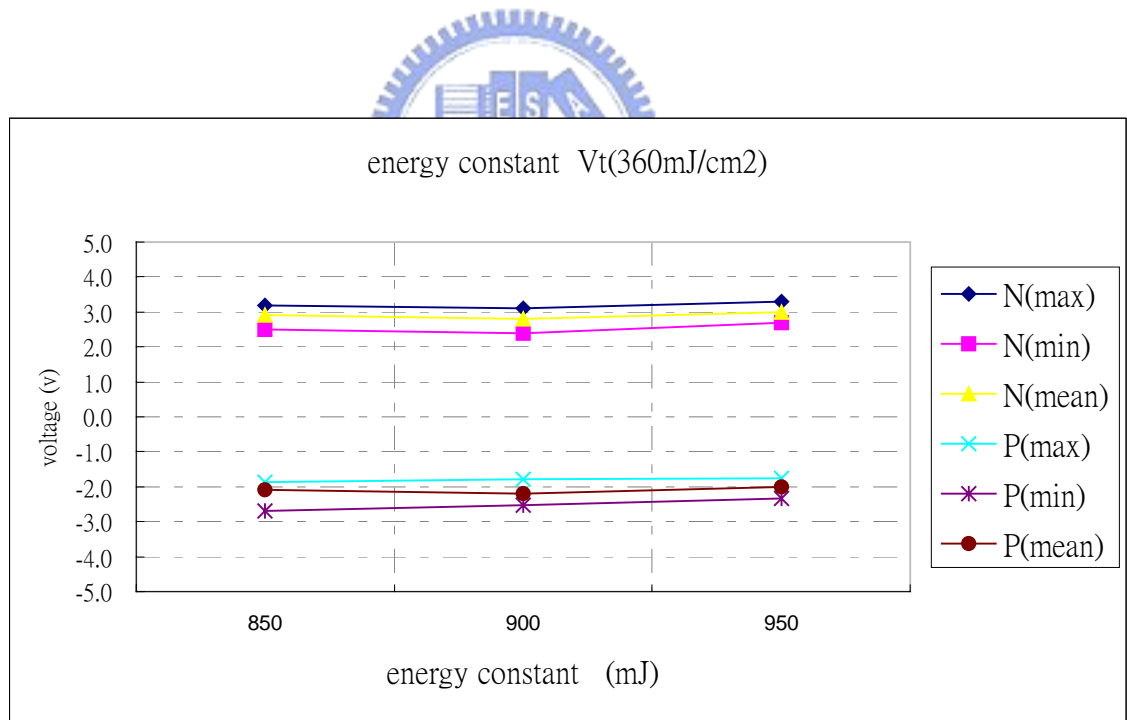


Fig. 3-38 The thresholds voltage of laser energy with pre treatment clean of HF+O3

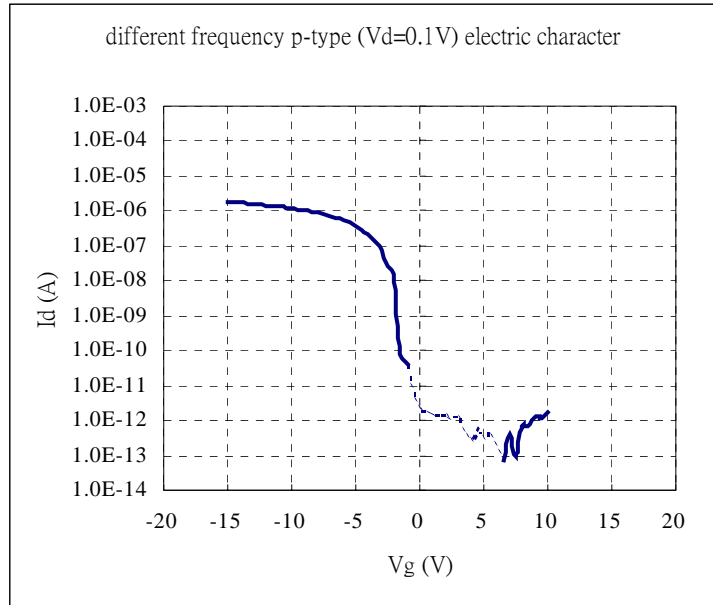


Fig. 3-39 The transfer characteristics of p type ELA poly-Silicon TFTs. Laser energy 900mJ, laser energy density 360mJ/cm², W/L = 6μm/12μm, V_t -2.1V, U_{fe} 101 cm²/V•sec, I_{off} 1.85E-13A, SS 0.21 and on/off current ratio 5.9E+6

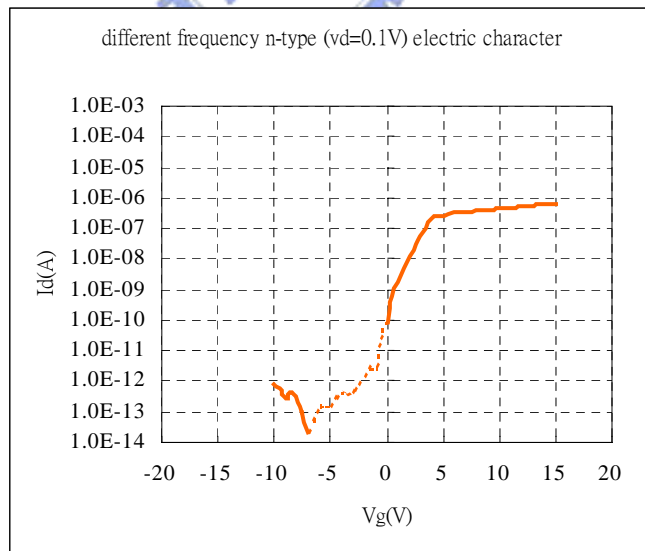


Fig. 3-40 The transfer characteristics of n type ELA poly-Silicon TFTs Laser energy 900mJ, laser energy density 360mJ/cm², W/L = 6μm/12μm, V_t 2.8V, U_{fe} 123 cm²/V•sec, I_{off} 2.02E-13A, SS 0.38 and on/off current ratio 8.9E+6

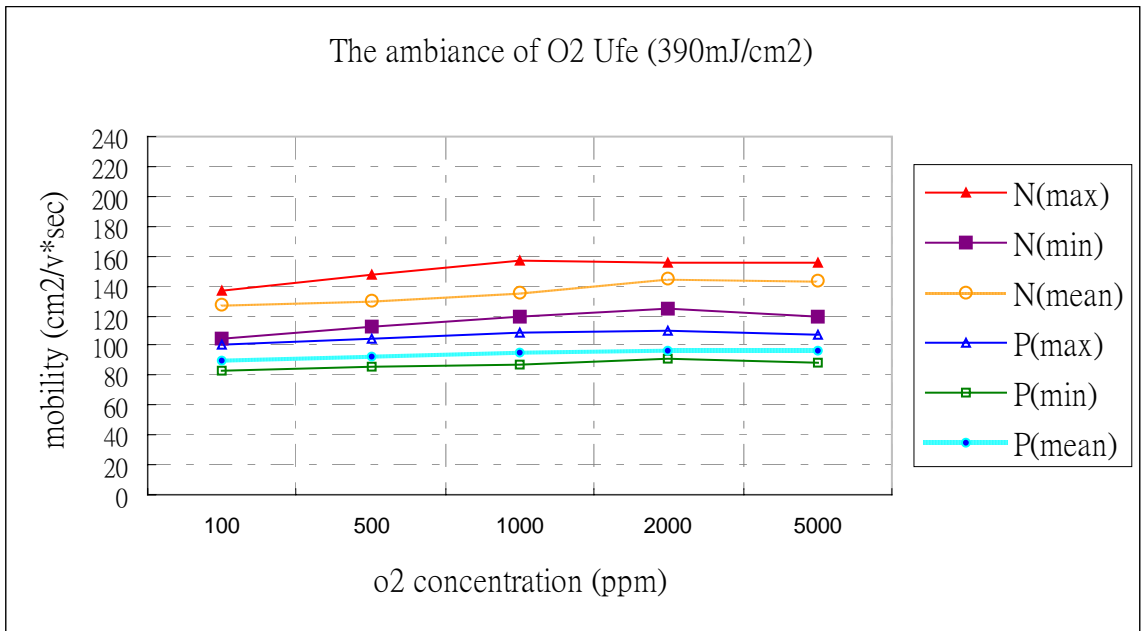


Fig. 3-41 The mobility of different laser irradiation ambience with pre treatment clean of HF1% for 30sec

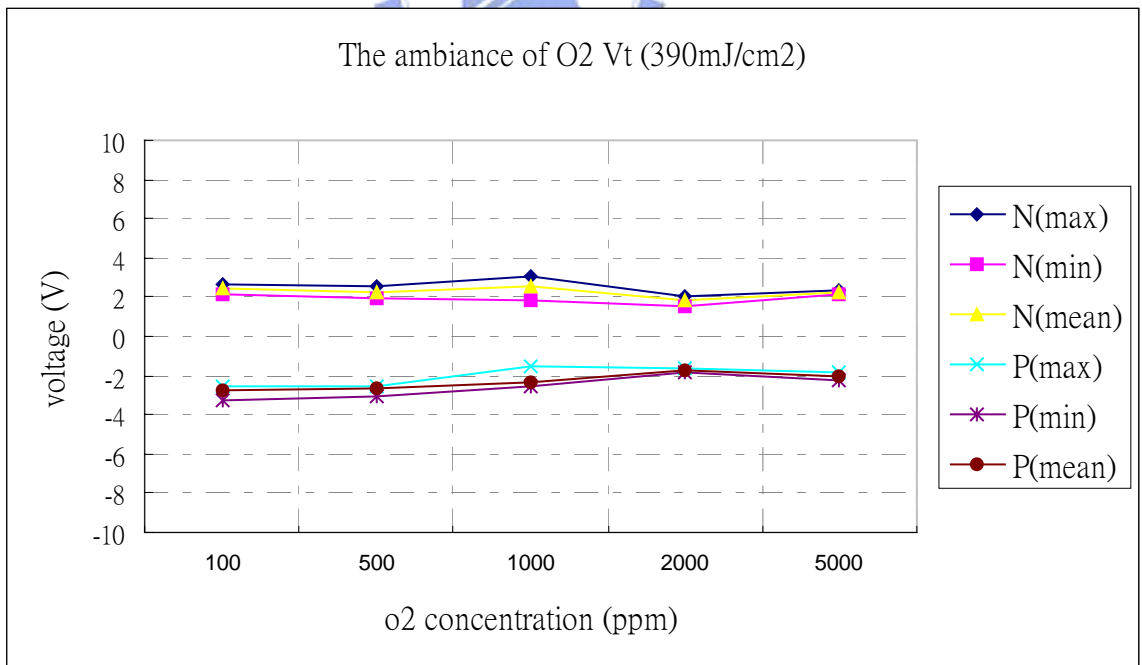


Fig. 3-42 The thresholds voltage of different laser irradiation ambience with pre treatment clean of HF1% for 30sec

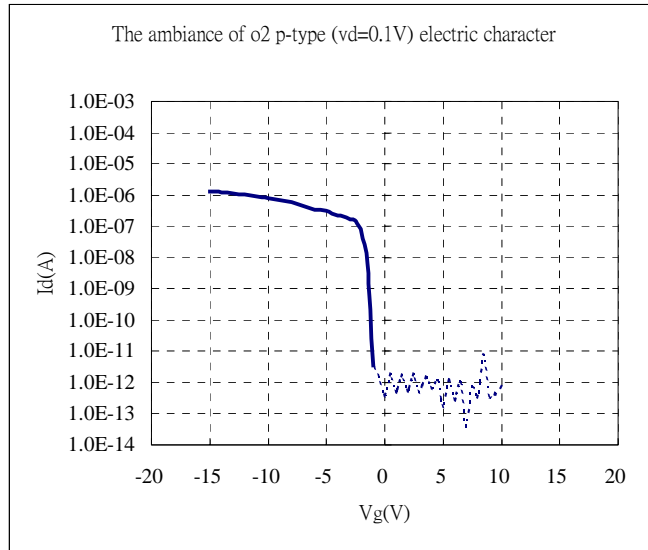


Fig. 3-43 The transfer characteristics of p type ELA poly-Silicon TFTs. The irradiation ambience with O₂ 2000ppm, laser energy density 390mJ/cm², W/L = 6μm/12μm, V_t -1.7V, U_{fe} 100 cm²/V•sec, I_{off} 1.18E-13A, SS 0.15 and on/off current ratio 1.1E+7

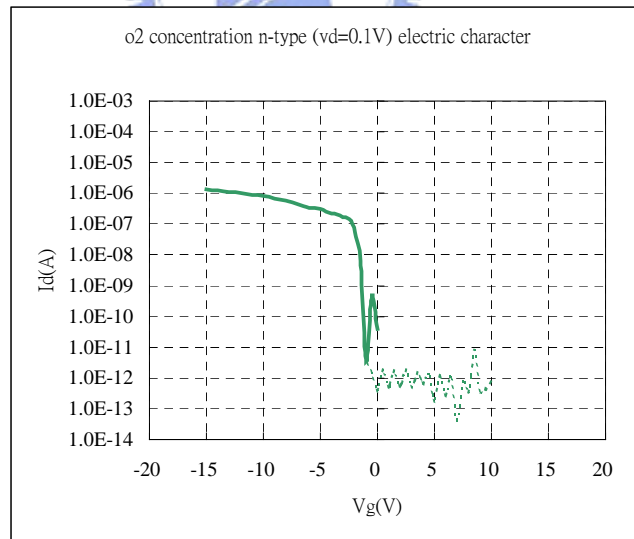


Fig. 3-44 The transfer characteristics of n type ELA poly-Silicon TFTs. The irradiation ambience with O₂ 2000ppm, laser energy density 390mJ/cm², W/L = 6μm/12μm, V_t 2.0V, U_{fe} 148 cm²/V•sec, I_{off} 2.94E-13A, SS 0.47 and on/off current ratio 8.3E+6